

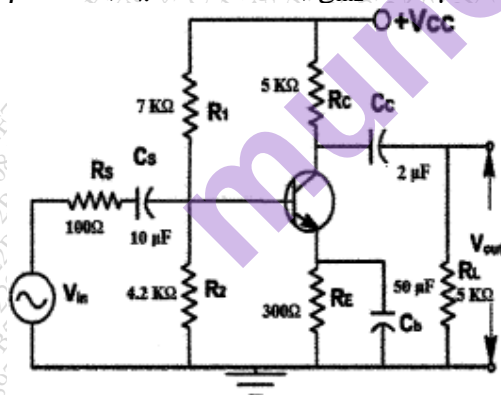
[Time: 3 Hours]

[Marks: 80]

Please check whether you have got the right question paper.

- N.B:**
1. **Q.1 is compulsory.**
 2. Solve **any three** questions from **Q.2 to Q.6**
 3. Assume suitable data

1. Write any **four** 20
 - (a) Explain high frequency equivalent circuit of BJT.
 - (b) Explain Barkhausen criteria
 - (c) Draw MOSFET differential amplifier with active load.
 - (d) Calculate max. power dissipation with and without heat sink
 $\theta_{JC} = 1.75^\circ \text{ C/W}$, $\theta_{CS} = 1^\circ \text{ C/W}$, $\theta_{CA} = 50^\circ \text{ C/W}$
 $\theta_{SA} = 5^\circ \text{ C/W}$, $T_{JMAX} = 150^\circ \text{ C}$ and $T_{AMB} = 30^\circ \text{ C}$
 - (e) Explain PNP diode.
2.
 - (a) Explain class B push pull power amplifier and cross over distortion also 10
derive expression for efficiency.
 - (b) Explain small signal analysis for MOSFET active load circuit 10
3. (a) Calculate lower cut off frequency for given circuit. 10
 $\beta = 80$, $r_\pi = 1.3 \text{ K}\Omega$, $g_{m2} = 50 \mu \text{ A/V}$, $C_\pi = 15 \text{ pF}$, $C_\mu = 1 \text{ pF}$



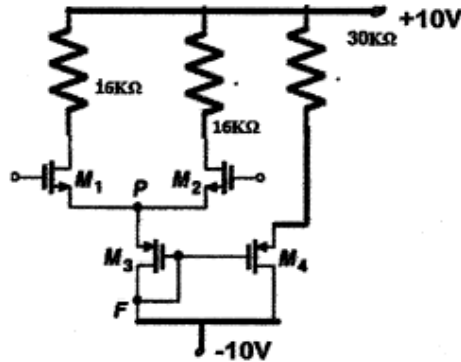
- (b) Explain working of SCR with V-I characteristics and its applications. 10
4. (a) Explain Hartley oscillator. Design the same for 50KHz. 10

Turn Over

- (b) Find
- I_Q
- for given circuit.

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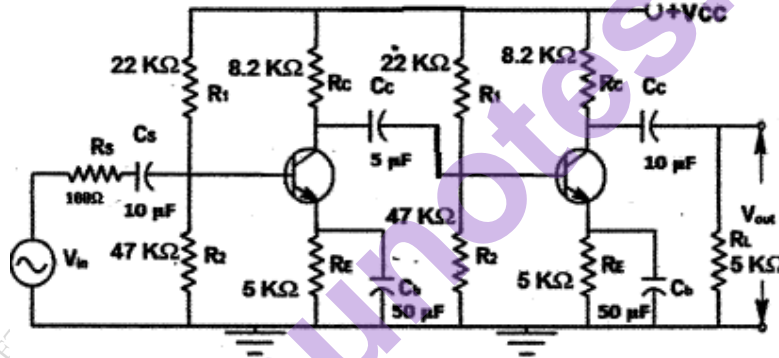
$K_{n1} = K_{n2} = 0.1 \text{ mA/V}^2$, $K_{n3} = K_{n4} = 0.3 \text{ mA/V}^2$, $V_{TN} = 1 \text{ V}$,
 $\lambda = 0$ for M_1, M_2, M_3 and $\lambda = 0.01/\text{V}$ for M_4



5. (a) Calculate bandwidth for two stage RC coupled CE amplifier.

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$\beta_1 = 100$, $\beta_2 = 150$, $r_{\pi 1} = r_{\pi 2} = 1.3 \text{ K}\Omega$, $g_{m1} = g_{m2} = 50 \text{ mA/V}$
 $C_{\pi 1} = C_{\pi 2} = 15 \text{ pF}$, $C_{\mu 1} = C_{\mu 2} = 1 \text{ pF}$



- (b) Explain feedback topologies with the help of neat block diagram.

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6. Solve any
- three**

20

- (a) Cascode MOSFET amplifier
 (b) UJT relaxation oscillator
 (c) Darlington configuration
 (d) Power BJTs
